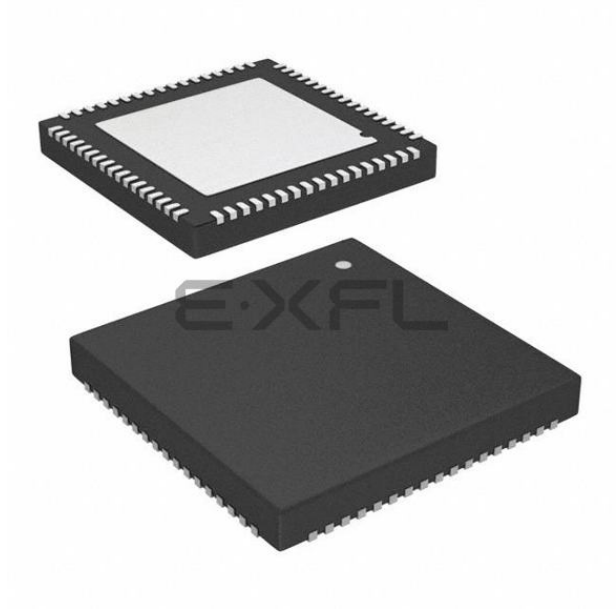


Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	8051
Core Size	8-Bit
Speed	67MHz
Connectivity	EBI/EMI, I²C, LINbus, SPI, UART/USART
Peripherals	CapSense, DMA, LCD, POR, PWM, WDT
Number of I/O	38
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	A/D 16x12b; D/A 4x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	68-VFQFN Exposed Pad
Supplier Device Package	68-QFN (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c3666lti-203t

In addition to the flexibility of the UDB array, PSoC also provides configurable digital blocks targeted at specific functions. For the CY8C36 family these blocks can include four 16-bit timers, counters, and PWM blocks; I^2C slave, master, and multi-master; FS USB; and Full CAN 2.0b.

For more details on the peripherals see the "Example Peripherals" section on page 44 of this data sheet. For information on UDBs, DSI, and other digital blocks, see the "Digital Subsystem" section on page 44 of this data sheet.

PSoC's analog subsystem is the second half of its unique configurability. All analog performance is based on a highly accurate absolute voltage reference with less than 0.1-percent error over temperature and voltage. The configurable analog subsystem includes:

- Analog muxes
- Comparators
- Voltage references
- ADC
- DACs
- DFB

All GPIO pins can route analog signals into and out of the device using the internal analog bus. This allows the device to interface up to 62 discrete analog signals. The heart of the analog subsystem is a fast, accurate, configurable delta-sigma ADC with these features:

- Less than 100 µV offset
- A gain error of 0.2 percent
- INL less than ±1 LSB
- DNL less than ±1 LSB
- SINAD better than 66 dB

This converter addresses a wide variety of precision analog applications, including some of the most demanding sensors.

The output of the ADC can optionally feed the programmable DFB through the DMA without CPU intervention. You can configure the DFB to perform IIR and FIR digital filters and several user-defined custom functions. The DFB can implement filters with up to 64 taps. It can perform a 48-bit multiply-accumulate (MAC) operation in one clock cycle.

Four high-speed voltage or current DACs support 8-bit output signals at an update rate of up to 8 Msps. They can be routed out of any GPIO pin. You can create higher resolution voltage PWM DAC outputs using the UDB array. This can be used to create a PWM DAC of up to 10 bits, at up to 48 kHz. The digital DACs in each UDB support PWM, PRS, or delta-sigma algorithms with programmable widths.

In addition to the ADC, DACs, and DFB, the analog subsystem provides multiple:

- Uncommitted opamps
- Configurable switched capacitor/continuous time (SC/CT) blocks. These support:
  - Transimpedance amplifiers
  - Programmable gain amplifiers
  - Mixers
  - Other similar analog components

See the "Analog Subsystem" section on page 56 of this data sheet for more details.

PSoC's 8051 CPU subsystem is built around a single-cycle pipelined 8051 8-bit processor running at up to 67 MHz. The CPU subsystem includes a programmable nested vector interrupt controller, DMA controller, and RAM. PSoC's nested vector interrupt controller provides low latency by allowing the CPU to vector directly to the first address of the interrupt service routine, bypassing the jump instruction required by other architectures. The DMA controller enables peripherals to exchange data without CPU involvement. This allows the CPU to run slower (saving power) or use those CPU cycles to improve the performance of firmware algorithms. The single cycle 8051 CPU runs ten times faster than a standard 8051 processor. The processor speed itself is configurable, allowing you to tune active power consumption for specific applications.

PSoC's nonvolatile subsystem consists of flash, byte-writeable EEPROM, and nonvolatile configuration options. It provides up to 64 KB of on-chip flash. The CPU can reprogram individual blocks of flash, enabling bootloaders. You can enable an ECC for high reliability applications. A powerful and flexible protection model secures the user's sensitive information, allowing selective memory block locking for read and write protection. Up to 2 KB of byte-writeable EEPROM is available on-chip to store application data. Additionally, selected configuration options such as boot speed and pin drive mode are stored in nonvolatile memory. This allows settings to activate immediately after POR.

The three types of PSoC I/O are extremely flexible. All I/Os have many drive modes that are set at POR. PSoC also provides up to four I/O voltage domains through the VDDIO pins. Every GPIO has analog I/O, LCD drive[3], CapSense[4], flexible interrupt generation, slew rate control, and digital I/O capability. The SIOs on PSoC allow V_{OH} to be set independently of V_{DDIO} when used as outputs. When SIOs are in input mode they are high impedance. This is true even when the device is not powered or when the pin voltage goes above the supply voltage. This makes the SIO ideally suited for use on an I^2C bus where the PSoC may not be powered when other devices on the bus are. The SIO pins also have high current sink capability for applications such as LED drives. The programmable input threshold feature of the SIO can be used to make the SIO function as a general purpose analog comparator. For devices with FS USB the USB physical interface is also provided (USBIO). When not using USB these pins may also be used for limited digital functionality and device programming. All of the features of the PSoC I/Os are covered in detail in the "I/O System and Routing" section on page 37 of this data sheet.

The PSoC device incorporates flexible internal clock generators, designed for high stability and factory trimmed for high accuracy. The internal main oscillator (IMO) is the clock base for the system, and has 1-percent accuracy at 3 MHz. The IMO can be configured to run from 3 MHz up to 62 MHz. Multiple clock derivatives can be generated from the main clock frequency to meet application needs. The device provides a PLL to generate clock frequencies up to 67 MHz from the IMO, external crystal, or external reference clock. It also contains a separate, very low-power internal low speed oscillator (ILO) for the sleep and watchdog timers. A 32.768-kHz external watch crystal is also supported for use in RTC applications. The clocks, together with programmable clock dividers, provide the flexibility to integrate most timing requirements.

4.2 Addressing Modes

The following addressing modes are supported by the 8051:

- Direct addressing: The operand is specified by a direct 8-bit address field. Only the internal RAM and the SFRs can be accessed using this mode.
- Indirect addressing: The instruction specifies the register which contains the address of the operand. The registers R0 or R1 are used to specify the 8-bit address, while the data pointer (DPTR) register is used to specify the 16-bit address.
- Register addressing: Certain instructions access one of the registers (R0 to R7) in the specified register bank. These instructions are more efficient because there is no need for an address field.
- Register specific instructions: Some instructions are specific to certain registers. For example, some instructions always act on the accumulator. In this case, there is no need to specify the operand.
- Immediate constants: Some instructions carry the value of the constants directly instead of an address.
- Indexed addressing: This type of addressing can be used only for a read of the program memory. This mode uses the Data Pointer as the base and the accumulator value as an offset to read a program memory.
- Bit addressing: In this mode, the operand is one of 256 bits.

4.3 Instruction Set

The 8051 instruction set is highly optimized for 8-bit handling and Boolean operations. The types of instructions supported include:

- Arithmetic instructions
- Logical instructions
- Data transfer instructions
- Boolean instructions
- Program branching instructions

4.3.1 Instruction Set Summary

4.3.1.1 Arithmetic Instructions

Arithmetic instructions support the direct, indirect, register, immediate constant, and register-specific instructions. Arithmetic modes are used for addition, subtraction, multiplication, division, increment, and decrement operations. Table 4-1 on page 15 lists the different arithmetic instructions.

Table 4-8. Interrupt Vector Table *(continued)*

#	Fixed Function	DMA	UDB
23	USB Bus Int	phub_termout1[7]	udb_intr[23]
24	USB Endpoint[0]	phub_termout1[8]	udb_intr[24]
25	USB Endpoint Data	phub_termout1[9]	udb_intr[25]
26	Reserved	phub_termout1[10]	udb_intr[26]
27	LCD	phub_termout1[11]	udb_intr[27]
28	DFB Int	phub_termout1[12]	udb_intr[28]
29	Decimator Int	phub_termout1[13]	udb_intr[29]
30	PHUB Error Int	phub_termout1[14]	udb_intr[30]
31	EEPROM Fault Int	phub_termout1[15]	udb_intr[31]

5. Memory

5.1 Static RAM

CY8C36 Static RAM (SRAM) is used for temporary data storage. Up to 8 KB of SRAM is provided and can be accessed by the 8051 or the DMA controller. See Memory Map on page 26. Simultaneous access of SRAM by the 8051 and the DMA controller is possible if different 4-KB blocks are accessed.

5.2 Flash Program Memory

Flash memory in PSoC devices provides nonvolatile storage for user firmware, user configuration data, bulk data storage, and optional ECC data. The main flash memory area contains up to 64 KB of user program space.

Up to an additional 8 KB of flash space is available for ECC. If ECC is not used this space can store device configuration data and bulk user data. User code may not be run out of the ECC flash memory section. ECC can correct one bit error and detect two bit errors per 8 bytes of firmware memory; an interrupt can be generated when an error is detected.

The CPU reads instructions located in flash through a cache controller. This improves instruction execution rate and reduces system power consumption by requiring less frequent flash access. The cache has 8 lines at 64 bytes per line for a total of 512 bytes. It is fully associative, automatically controls flash power, and can be enabled or disabled. If ECC is enabled, the cache controller also performs error checking and correction, and interrupt generation.

Flash programming is performed through a special interface and preempts code execution out of flash. The flash programming interface performs flash erasing, programming and setting code protection levels. Flash in-system serial programming (ISSP), typically used for production programming, is possible through both the SWD and JTAG interfaces. In-system programming, typically used for bootloaders, is also possible using serial interfaces such as I^2C, USB, UART, and SPI, or any communications protocol.

5.3 Flash Security

All PSoC devices include a flexible flash-protection model that prevents access and visibility to on-chip flash memory. This prevents duplication or reverse engineering of proprietary code. Flash memory is organized in blocks, where each block contains 256 bytes of program or data and 32 bytes of ECC or configuration data. A total of up to 256 blocks is provided on 64-KB flash devices.

The device offers the ability to assign one of four protection levels to each row of flash. Table 5-1 lists the protection modes available. Flash protection levels can only be changed by performing a complete flash erase. The Full Protection and Field Upgrade settings disable external access (through a debugging tool such as PSoC Creator, for example). If your application requires code update through a boot loader, then use the Field Upgrade setting. Use the Unprotected setting only when no security is needed in your application. The PSoC device also offers an advanced security feature called Device Security that permanently disables all test, programming, and debug ports, protecting your application from external access (see Device Security on page 68). For information about how to take full advantage of the security features in PSoC, see the PSoC 3 TRM.

Table 5-1. Flash Protection

Protection Setting	Allowed	Not Allowed
Unprotected	External read and write + internal read and write	–
Factory Upgrade	External write + internal read and write	External read
Field Upgrade	Internal read and write	External read and write
Full Protection	Internal read	External read and write + internal write

Disclaimer

Note the following details of the flash code protection features on Cypress devices.

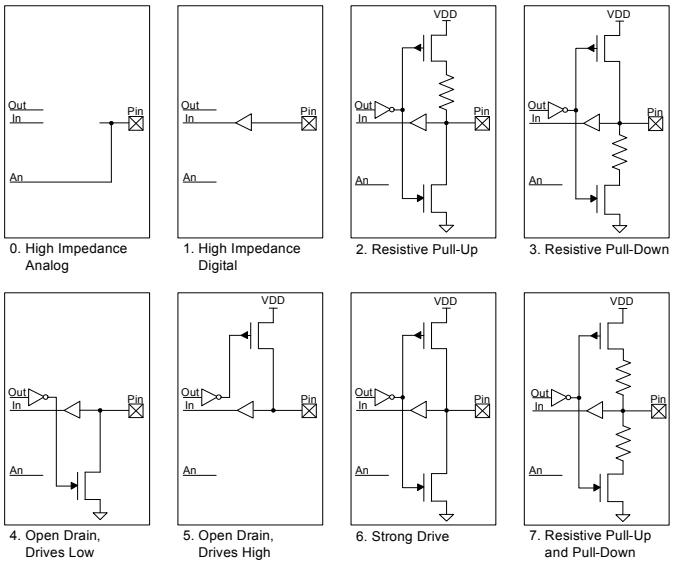
Cypress products meet the specifications contained in their particular Cypress data sheets. Cypress believes that its family of products is one of the most secure families of its kind on the market today, regardless of how they are used. There may be methods, unknown to Cypress, that can breach the code protection features. Any of these methods, to our knowledge, would be dishonest and possibly illegal. Neither Cypress nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as “unbreakable.”

Cypress is willing to work with the customer who is concerned about the integrity of their code. Code protection is constantly evolving. We at Cypress are committed to continuously improving the code protection features of our products.

6.4.1 Drive Modes

Each GPIO and SIO pin is individually configurable into one of the eight drive modes listed in Table 6-3. Three configuration bits are used for each pin (DM[2:0]) and set in the PRTxDM[2:0] registers. Figure 6-12 depicts a simplified pin view based on each of the eight drive modes. Table 6-3 shows the I/O pin's drive state based on the port data register value or digital array signal if bypass mode is selected. Note that the actual I/O pin voltage is determined by a combination of the selected drive mode and the load at the pin. For example, if a GPIO pin is configured for resistive pull-up mode and driven high while the pin is floating, the voltage measured at the pin is a high logic state. If the same GPIO pin is externally tied to ground then the voltage unmeasured at the pin is a low logic state.

Figure 6-12. Drive Mode



The 'Out' connection is driven from either the Digital System (when the Digital Output terminal is connected) or the Data Register (when HW connection is disabled).
The 'In' connection drives the Pin State register, and the Digital System if the Digital Input terminal is enabled and connected.
The 'An' connection connects to the Analog System.

Table 6-3. Drive Modes

Diagram	Drive Mode	PRTxDM2	PRTxDM1	PRTxDM0	PRTxDR = 1	PRTxDR = 0
0	High impedance analog	0	0	0	High Z	High Z
1	High impedance digital	0	0	1	High Z	High Z
2	Resistive pull-up[18]	0	1	0	Res High (5K)	Strong Low
3	Resistive pull-down[18]	0	1	1	Strong High	Res Low (5K)
4	Open drain, drives low	1	0	0	High Z	Strong Low
5	Open drain, drive high	1	0	1	Strong High	High Z
6	Strong drive	1	1	0	Strong High	Strong Low
7	Resistive pull-up and pull-down[18]	1	1	1	Res High (5K)	Res Low (5K)

Note
18. Resistive pull-up and pull-down are not available with SIO in regulated output mode.

The USBIO pins (P15[7] and P15[6]), when enabled for I/O mode, have limited drive mode control. The drive mode is set using the PRT15.DM0[7, 6] register. A resistive pull option is also available at the USBIO pins, which can be enabled using the PRT15.DM1[7, 6] register. When enabled for USB mode, the drive mode control has no impact on the configuration of the USB pins. Unlike the GPIO and SIO configurations, the port wide configuration registers do not configure the USB drive mode bits. Table 6-4 shows the drive mode configuration for the USBIO pins.

Table 6-4. USBIO Drive Modes (P15[7] and P15[6])

PRT15.DM1[7,6] Pull up enable	PRT15.DM0[7,6] Drive Mode enable	PRT15.DR[7,6] = 1	PRT15.DR[7,6] = 0	Description
0	0	High Z	Strong Low	Open Drain, Strong Low
0	1	Strong High	Strong Low	Strong Outputs
1	0	Res High (5k)	Strong Low	Resistive Pull Up, Strong Low
1	1	Strong High	Strong Low	Strong Outputs

- High Impedance Analog

  The default reset state with both the output driver and digital input buffer turned off. This prevents any current from flowing in the I/O's digital input buffer due to a floating voltage. This state is recommended for pins that are floating or that support an analog voltage. High impedance analog pins do not provide digital input functionality.

  To achieve the lowest chip current in sleep modes, all I/Os must either be configured to the high impedance analog mode, or have their pins driven to a power supply rail by the PSoC device or by external circuitry.

- High Impedance Digital

  The input buffer is enabled for digital signal input. This is the standard high impedance (HiZ) state recommended for digital inputs.

- Resistive pull-up or resistive pull-down

  Resistive pull-up or pull-down, respectively, provides a series resistance in one of the data states and strong drive in the other. Pins can be used for digital input and output in these modes. Interfacing to mechanical switches is a common application for these modes. Resistive pull-up and pull-down are not available with SIO in regulated output mode.

- Open Drain, Drives High and Open Drain, Drives Low

  Open drain modes provide high impedance in one of the data states and strong drive in the other. Pins can be used for digital input and output in these modes. A common application for these modes is driving the I^2C bus signal lines.

- Strong Drive

  Provides a strong CMOS output drive in either high or low state. This is the standard output mode for pins. Strong Drive mode pins must not be used as inputs under normal circumstances. This mode is often used to drive digital output signals or external FETs.

- Resistive pull-up and pull-down

  Similar to the resistive pull-up and resistive pull-down modes except the pin is always in series with a resistor. The high data state is pull-up while the low data state is pull-down. This mode is most often used when other signals that may cause shorts can drive the bus. Resistive pull-up and pull-down are not available with SIO in regulated output mode.

6.4.2 Pin Registers

Registers to configure and interact with pins come in two forms that may be used interchangeably.

All I/O registers are available in the standard port form, where each bit of the register corresponds to one of the port pins. This register form is efficient for quickly reconfiguring multiple port pins at the same time.

I/O registers are also available in pin form, which combines the eight most commonly used port register bits into a single register for each pin. This enables very fast configuration changes to individual pins with a single register write.

6.4.3 Bidirectional Mode

High speed bidirectional capability allows pins to provide both the high impedance digital drive mode for input signals and a second user selected drive mode such as strong drive (set using PRT×DM[2:0] registers) for output signals on the same pin, based on the state of an auxiliary control bus signal. The bidirectional capability is useful for processor busses and communications interfaces such as the SPI Slave MISO pin that requires dynamic hardware control of the output buffer.

The auxiliary control bus routes up to 16 UDB or digital peripheral generated output enable signals to one or more pins.

6.4.4 Slew Rate Limited Mode

GPIO and SIO pins have fast and slow output slew rate options for strong and open drain drive modes, not resistive drive modes. Because it results in reduced EMI, the slow edge rate option is recommended for signals that are not speed critical, generally less than 1 MHz. The fast slew rate is for signals between 1 MHz and 33 MHz. The slew rate is individually configurable for each pin, and is set by the PRT×SLW registers.

9.8 CSP Package Bootloader

A factory-installed bootloader program is included in all devices with CSP packages. The bootloader is compatible with PSoC Creator 3.0 bootloadable project files and has the following features:

- I^2C-based
- SCLK and SDAT available at P1[6] and P1[7], respectively
- External pull-up resistors required
- I^2C slave, address 4, data rate = 100 kbps
- Single application
- Wait two seconds for bootload command
- Other bootloader options are as set by the PSoC Creator 3.0 Bootloader Component default
- Occupies the bottom 9K of flash

For more information on this bootloader, see the following Cypress application notes:

- AN89611 – PSoC® 3 AND PSoC 5LP - Getting Started With Chip Scale Packages (CSP)
- AN73854 – PSoC 3 and PSoC 5 LP Introduction to Bootloaders
- AN60317 – PSoC 3 and PSoC 5 LP I^2C Bootloader

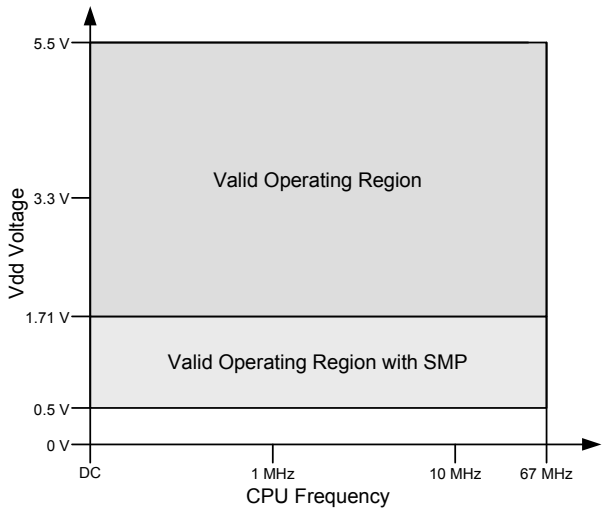
Note that a PSOC Creator bootloadable project must be associated with .hex and .elf files for a bootloader project that is configured for the target device. Bootloader .hex and .elf files can be found at www.cypress.com/go/PSoC3datasheet.

The factory-installed bootloader can be overwritten using JTAG or SWD programming.

Table 11-3. AC Specifications[37]

Parameter	Description	Conditions	Min	Typ	Max	Units
F_{CPU}	CPU frequency	1.71 V ≤ V_{DDD} ≤ 5.5 V	DC	–	67.01	MHz
F_{BUSCLK}	Bus frequency	1.71 V ≤ V_{DDD} ≤ 5.5 V	DC	–	67.01	MHz
Svdd	V_{DD} ramp rate		–	–	0.066	V/µs
T_{IO_INIT}	Time from V_{DDD}/V_{DDA}/V_{CCD}/V_{CCA} ≥ IPOR to I/O ports set to their reset states		–	–	10	µs
$T_{STARTUP}$	Time from V_{DDD}/V_{DDA}/V_{CCD}/V_{CCA} ≥ PRES to CPU executing code at reset vector	V_{CCA}/V_{DDA} = regulated from V_{DDA}/V_{DDD}, no PLL used, fast IMO boot mode (48 MHz typ.)	–	–	40	µs
		V_{CCA}/V_{CCD} = regulated from V_{DDA}/V_{DDD}, no PLL used, slow IMO boot mode (12 MHz typ.)	–	–	74	µs
T_{SLEEP}	Wakeup from sleep mode – Application of non–LVD interrupt to beginning of execution of next CPU instruction		–	–	15	µs
$T_{HIBERNATE}$	Wakeup from hibernate mode – Application of external interrupt to beginning of execution of next CPU instruction		–	–	100	µs

Figure 11-4. F_{CPU} vs. V_{DD}



Note
37. Based on device characterization (Not production tested).

11.3.3 Inductive Boost Regulator

Unless otherwise specified, operating conditions are: V_{BAT} = 0.5 V–3.6 V, V_{OUT} = 1.8 V–5.0 V, I_{OUT} = 0 mA–50 mA, L_{BOOST} = 4.7 µH–22 µH, C_{BOOST} = 22 µF || 3 × 1.0 µF || 3 × 0.1 µF, C_{BAT} = 22 µF, I_F = 1.0 A. Unless otherwise specified, all charts and graphs show typical values.

Table 11-6. Inductive Boost Regulator DC Specifications

Parameter	Description	Conditions		Min	Typ	Max	Units
V_{OUT}	Boost output voltage[38]	vsel = 1.8 V in register BOOST_CR0		1.71	1.8	1.89	V
		vsel = 1.9 V in register BOOST_CR0		1.81	1.90	2.00	V
		vsel = 2.0 V in register BOOST_CR0		1.90	2.00	2.10	V
		vsel = 2.4 V in register BOOST_CR0		2.16	2.40	2.64	V
		vsel = 2.7 V in register BOOST_CR0		2.43	2.70	2.97	V
		vsel = 3.0 V in register BOOST_CR0		2.70	3.00	3.30	V
		vsel = 3.3 V in register BOOST_CR0		2.97	3.30	3.63	V
		vsel = 3.6 V in register BOOST_CR0		3.24	3.60	3.96	V
		vsel = 5.0 V in register BOOST_CR0		4.50	5.00	5.50	V
V_{BAT}	Input voltage to boost[39]	I_{OUT} = 0 mA–5 mA	vsel = 1.8 V–2.0 V, T_A = 0 °C–70 °C	0.5	–	0.8	V
		I_{OUT} = 0 mA–15 mA	vsel = 1.8 V–5.0 V[40], T_A = –10 °C–85 °C	1.6	–	3.6	V
		I_{OUT} = 0 mA–25 mA	vsel = 1.8 V–2.7 V, T_A = –10 °C–85 °C	0.8	–	1.6	V
		I_{OUT} = 0 mA–50 mA	vsel = 1.8 V–3.3 V[40], T_A = –40 °C–85 °C	1.8	–	2.5	V
			vsel = 1.8 V–3.3 V[40], T_A = –10 °C–85 °C	1.3	–	2.5	V
			vsel = 2.5 V–5.0 V[40], T_A = –10 °C–85 °C	2.5	–	3.6	V
I_{OUT}	Output current	T_A = 0 °C–70 °C	V_{BAT} = 0.5 V–0.8 V	0	–	5	mA
		T_A = –10 °C–85 °C	V_{BAT} = 1.6 V–3.6 V	0	–	15	mA
			V_{BAT} = 0.8 V–1.6 V	0	–	25	mA
			V_{BAT} = 1.3 V–2.5 V	0	–	50	mA
			V_{BAT} = 2.5 V–3.6 V	0	–	50	mA
		T_A = –40 °C–85 °C	V_{BAT} = 1.8 V–2.5 V	0	–	50	mA
I_{LPK}	Inductor peak current			–	–	700	mA
I_Q	Quiescent current	Boost active mode		–	250	–	µA
		Boost sleep mode, I_{OUT} < 1 µA		–	25	–	µA
Reg_{LOAD}	Load regulation			–	–	10	%
Reg_{LINE}	Line regulation			–	–	10	%

Notes
38. Listed vsel options are characterized. Additional vsel options are valid and guaranteed by design.
39. The boost will start at all valid V_{BAT} conditions including down to V_{BAT} = 0.5 V.
40. If V_{BAT} is greater than or equal to V_{OUT} boost setting, then V_{OUT} will be less than V_{BAT} due to resistive losses in the boost circuit.

Table 11-12. SIO AC Specifications *(continued)*

Parameter	Description	Conditions	Min	Typ	Max	Units
Fsioout	SIO output operating frequency					
	2.7 V < V_{DDIO} < 5.5 V, Unregulated output (GPIO) mode, fast strong drive mode	90/10% V_{DDIO} into 25 pF	–	–	33	MHz
	1.71 V < V_{DDIO} < 2.7 V, Unregulated output (GPIO) mode, fast strong drive mode	90/10% V_{DDIO} into 25 pF	–	–	16	MHz
	3.3 V < V_{DDIO} < 5.5 V, Unregulated output (GPIO) mode, slow strong drive mode	90/10% V_{DDIO} into 25 pF	–	–	5	MHz
	1.71 V < V_{DDIO} < 3.3 V, Unregulated output (GPIO) mode, slow strong drive mode	90/10% V_{DDIO} into 25 pF	–	–	4	MHz
	2.7 V < V_{DDIO} < 5.5 V, Regulated output mode, fast strong drive mode	Output continuously switching into 25 pF	–	–	20	MHz
	1.71 V < V_{DDIO} < 2.7 V, Regulated output mode, fast strong drive mode	Output continuously switching into 25 pF	–	–	10	MHz
	1.71 V < V_{DDIO} < 5.5 V, Regulated output mode, slow strong drive mode	Output continuously switching into 25 pF	–	–	2.5	MHz
Fsioin	SIO input operating frequency					
	1.71 V ≤ V_{DDIO} ≤ 5.5 V	90/10% V_{DDIO}	–	–	33	MHz

Figure 11-20. SIO Output Rise and Fall Times, Fast Strong Mode, V_{DDIO} = 3.3 V, 25 pF Load

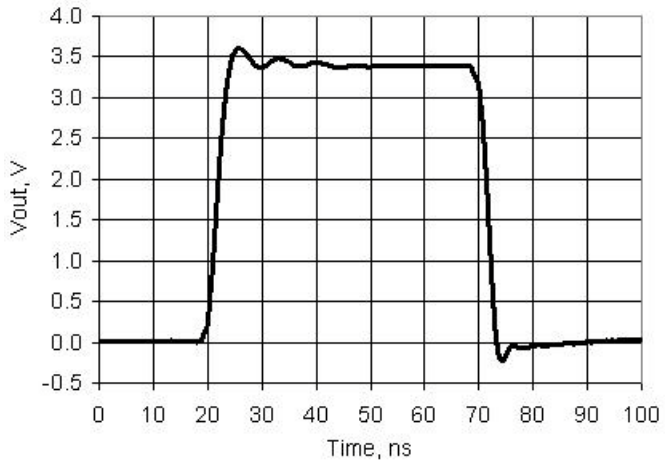


Figure 11-21. SIO Output Rise and Fall Times, Slow Strong Mode, V_{DDIO} = 3.3 V, 25 pF Load

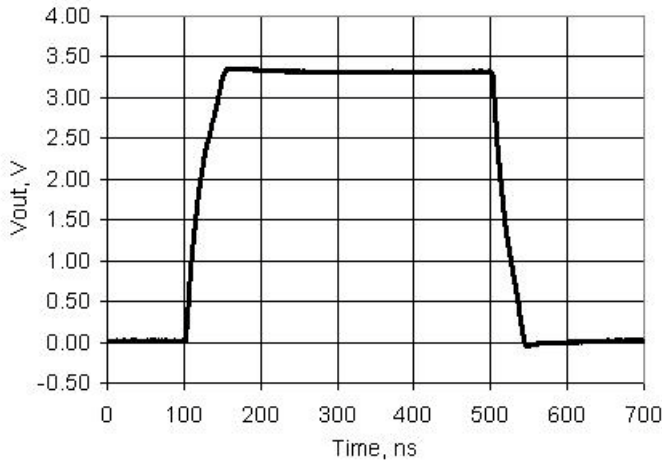


Table 11-13. SIO Comparator Specifications[49]

Parameter	Description	Conditions	Min	Typ	Max	Units
Vos	Offset voltage	V_{DDIO} = 2 V	–	–	68	mV
		V_{DDIO} = 2.7 V	–	–	72	
		V_{DDIO} = 5.5 V	–	–	82	
TCVos	Offset voltage drift with temp		–	–	250	µV/°C
CMRR	Common mode rejection ratio	V_{DDIO} = 2 V	30	–	–	dB
		V_{DDIO} = 2.7 V	35	–	–	
		V_{DDIO} = 5.5 V	40	–	–	
Tresp	Response time		–	–	30	ns

11.4.3 USBIO

For operation in GPIO mode, the standard range for V_{DDD} applies, see Device Level Specifications on page 72.

Table 11-14. USBIO DC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
Rusbi	USB D+ pull-up resistance	With idle bus	0.900	–	1.575	kΩ
Rusba	USB D+ pull-up resistance	While receiving traffic	1.425	–	3.090	kΩ
Vohusb	Static output high	15 kΩ ±5% to Vss, internal pull-up enabled	2.8	–	3.6	V
Volusb	Static output low	15 kΩ ±5% to Vss, internal pull-up enabled	–	–	0.3	V
Vihgpio	Input voltage high, GPIO mode	$V_{DDD} \geq 3$ V	2	–	–	V
Vilgpio	Input voltage low, GPIO mode	$V_{DDD} \geq 3$ V	–	–	0.8	V
Vohgpio	Output voltage high, GPIO mode	I_{OH} = 4 mA, $V_{DDD} \geq 3$ V	2.4	–	–	V
Volgpio	Output voltage low, GPIO mode	I_{OL} = 4 mA, $V_{DDD} \geq 3$ V	–	–	0.3	V
Vdi	Differential input sensitivity	|(D+)–(D–)|	–	–	0.2	V
Vcm	Differential input common mode range	–	0.8	–	2.5	V
Vse	Single ended receiver threshold	–	0.8	–	2	V
Rps2	PS/2 pull-up resistance	In PS/2 mode, with PS/2 pull-up enabled	3	–	7	kΩ
Rext	External USB series resistor	In series with each USB pin	21.78 (–1%)	22	22.22 (+1%)	Ω
Zo	USB driver output impedance	Including Rext	28	–	44	Ω
C_{IN}	USB transceiver input capacitance		–	–	20	pF
I_{IL}[49]	Input leakage current (absolute value)	25 °C, V_{DDD} = 3.0 V	–	–	2	nA

Note
49. Based on device characterization (Not production tested).

Figure 11-24. USBIO Output Rise and Fall Times, GPIO Mode, V_{DDD} = 3.3 V, 25 pF Load

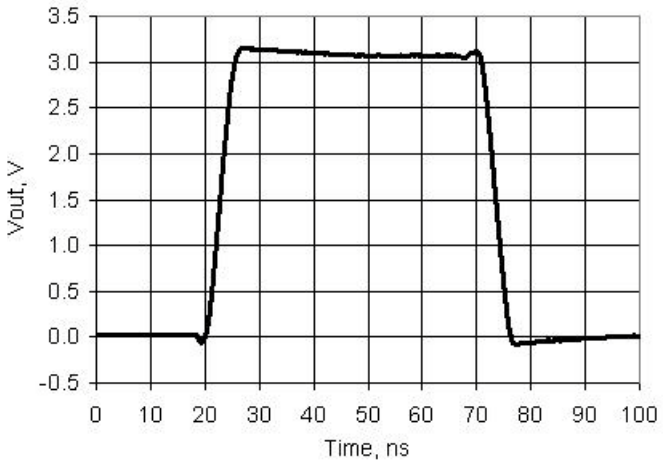


Table 11-16. USB Driver AC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
Tr	Transition rise time		–	–	20	ns
Tf	Transition fall time		–	–	20	ns
TR	Rise/fall time matching	V_{USB_5}, $V_{USB\_3.3}$, see USB DC Specifications on page 107	90%	–	111%	
Vcrs	Output signal crossover voltage		1.3	–	2	V

11.4.4 XRES

Table 11-17. XRES DC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
V_{IH}	Input voltage high threshold		0.7 × V_{DDIO}	–	–	V
V_{IL}	Input voltage low threshold		–	–	0.3 × V_{DDIO}	V
Rpullup	Pull-up resistor		3.5	5.6	8.5	kΩ
C_{IN}	Input capacitance[50]		–	3	–	pF
V_H	Input voltage hysteresis (Schmitt–Trigger)[50]		–	100	–	mV
Idiode	Current through protection diode to V_{DDIO} and V_{SSIO}		–	–	100	µA

Table 11-18. XRES AC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
T_{RESET}	Reset pulse width		1	–	–	µs

11.5 Analog Peripherals

Specifications are valid for –40 °C ≤ T_A ≤ 85 °C and T_J ≤ 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

11.5.1 Opamp

Table 11-19. Opamp DC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
V_{IOFF}	Input offset voltage		–	–	2	mV
V_{OS}	Input offset voltage		–	–	2.5	mV
		Operating temperature –40 °C to 70 °C	–	–	2	mV
TCV_{OS}	Input offset voltage drift with temperature	Power mode = high	–	–	±30	µV / °C
Ge1	Gain error, unity gain buffer mode	Rload = 1 kΩ	–	–	±0.1	%
C_{IN}	Input capacitance	Routing from pin	–	–	18	pF
V_O	Output voltage range	1 mA, source or sink, power mode = high	V_{SSA} + 0.05	–	V_{DDA} – 0.05	V
I_{OUT}	Output current capability, source or sink	V_{SSA} + 500 mV ≤ Vout ≤ V_{DDA} –500 mV, V_{DDA} > 2.7 V	25	–	–	mA
		V_{SSA} + 500 mV ≤ Vout ≤ V_{DDA} –500 mV, 1.7 V = V_{DDA} ≤ 2.7 V	16	–	–	mA
I_{DD}	Quiescent current	Power mode = min	–	250	400	uA
		Power mode = low	–	250	400	uA
		Power mode = med	–	330	950	uA
		Power mode = high	–	1000	2500	uA
CMRR	Common mode rejection ratio		80	–	–	dB
PSRR	Power supply rejection ratio	V_{DDA} ≥ 2.7 V	85	–	–	dB
		V_{DDA} < 2.7 V	70	–	–	dB
I_{IB}	Input bias current[50]	25 °C	–	10	–	pA

Note
50. Based on device characterization (Not production tested).

11.5.3 Voltage Reference

Table 11-24. Voltage Reference Specifications

See also ADC external reference specifications in *Section 11.5.2*.

Parameter	Description	Conditions		Min	Typ	Max	Units
V_{REF}[56]	Precision reference voltage	Initial trimming, 25 °C		1.023 (–0.1%)	1.024	1.025 (+0.1%)	V
	After typical PCB assembly, post reflow	Typical (non-optimized) board layout and 250 °C solder reflow. Device may be calibrated after assembly to improve performance	–40 °C	–	±0.5	–	%
			25 °C	–	±0.2	–	%
			85 °C	–	±0.2	–	%
	Temperature drift[57]	Box method		–	–	30	ppm/°C
	Long term drift			–	100	–	ppm/khr
	Thermal cycling drift (stability)[57, 58]			–	100	–	ppm

Figure 11-34. Voltage Reference vs. Temperature and V_{CCA}

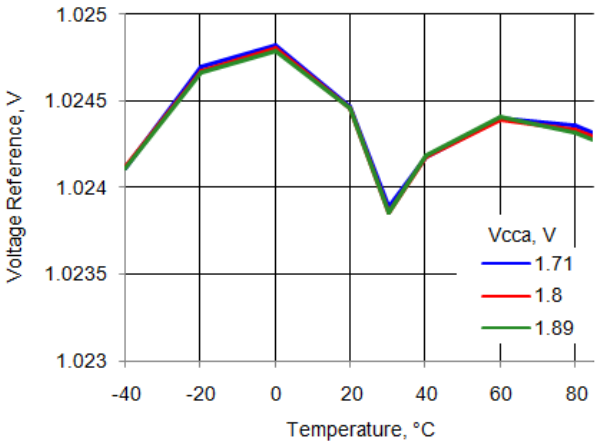
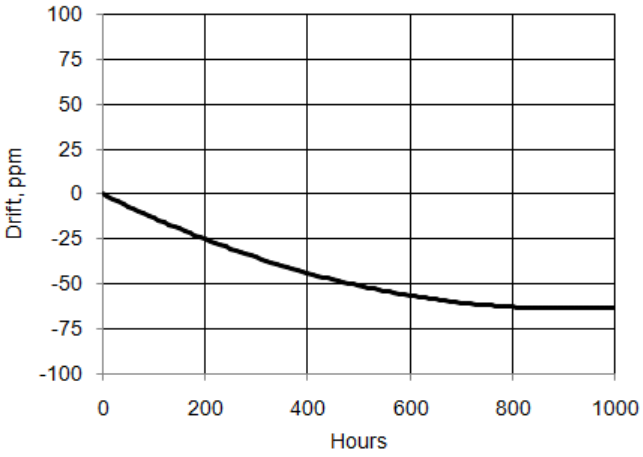


Figure 11-35. Voltage Reference Long-Term Drift



11.5.4 Analog Globals

Table 11-25. Analog Globals Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
Rppag	Resistance pin-to-pin through P2[4], AGL0, DSM INP, AGL1, P2[5][59]	V_{DDA} = 3 V	–	1472	2200	Ω
Rppmuxbus	Resistance pin-to-pin through P2[3], amuxbusL, P2[4][59]	V_{DDA} = 3 V	–	706	1100	Ω

Notes
56. V_{REF} is measured after packaging, and thus accounts for substrate and die attach stresses.
57. Based on device characterization (Not production tested).
58. After eight full cycles between –40 °C and 100 °C.
59. The resistance of the analog global and analog mux bus is high if $V_{DDA} \leq 2.7$ V, and the chip is in either sleep or hibernate mode. Use of analog global and analog mux bus under these conditions is not recommended.

11.5.7 Voltage Digital to Analog Converter (VDAC)

See the VDAC component datasheet in PSoC Creator for full electrical specifications and APIs.

Unless otherwise specified, all charts and graphs show typical values.

Table 11-30. VDAC DC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
	Resolution		–	8	–	bits
INL1	Integral nonlinearity	1 V scale	–	±2.1	±2.5	LSB
INL4	Integral nonlinearity[62]	4 V scale	–	±2.1	±2.5	LSB
DNL1	Differential nonlinearity	1 V scale	–	±0.3	±1	LSB
DNL4	Differential nonlinearity[62]	4 V scale	–	±0.3	±1	LSB
Rout	Output resistance	1 V scale	–	4	–	kΩ
		4 V scale	–	16	–	kΩ
V_{OUT}	Output voltage range, code = 255	1 V scale	–	1.02	–	V
		4 V scale, V_{DDA} = 5 V	–	4.08	–	V
	Monotonicity		–	–	Yes	–
V_{OS}	Zero scale error		–	0	±0.9	LSB
Eg	Gain error	1 V scale	–	–	±2.5	%
		4 V scale	–	–	±2.5	%
TC_Eg	Temperature coefficient, gain error	1 V scale	–	–	0.03	%FSR / °C
		4 V scale	–	–	0.03	%FSR / °C
I_{DD}	Operating current	Low speed mode	–	–	100	µA
		High speed mode	–	–	500	µA

Figure 11-50. VDAC INL vs Input Code, 1 V Mode

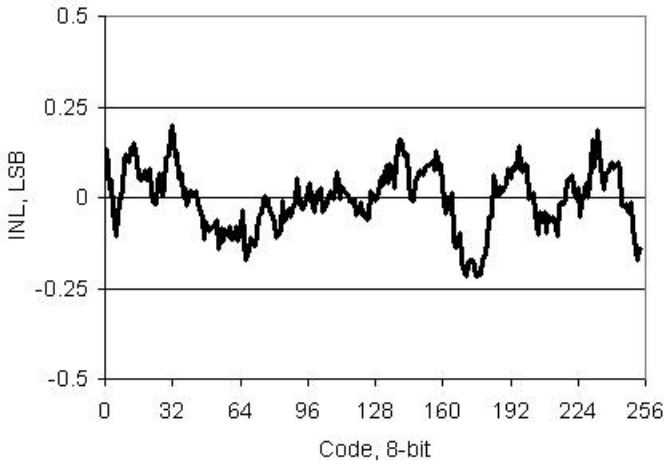
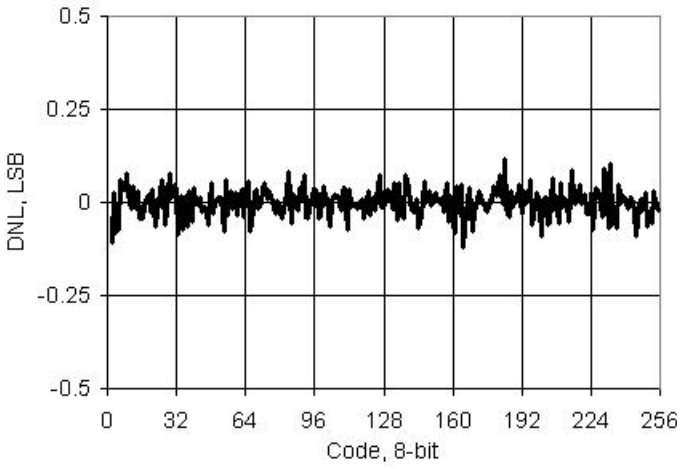


Figure 11-51. VDAC DNL vs Input Code, 1 V Mode



Note
62. Based on device characterization (Not production tested).

Figure 11-52. VDAC INL vs Temperature, 1 V Mode

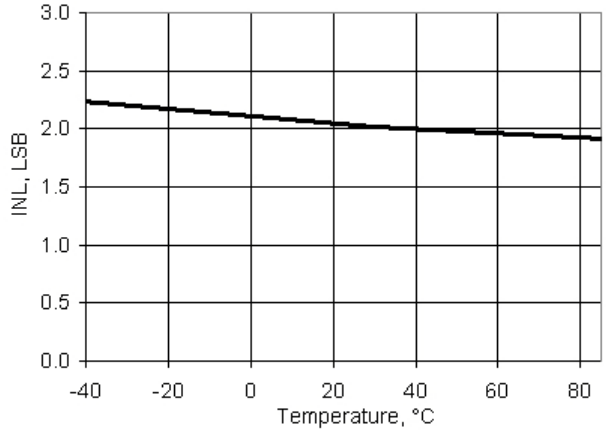


Figure 11-53. VDAC DNL vs Temperature, 1 V Mode

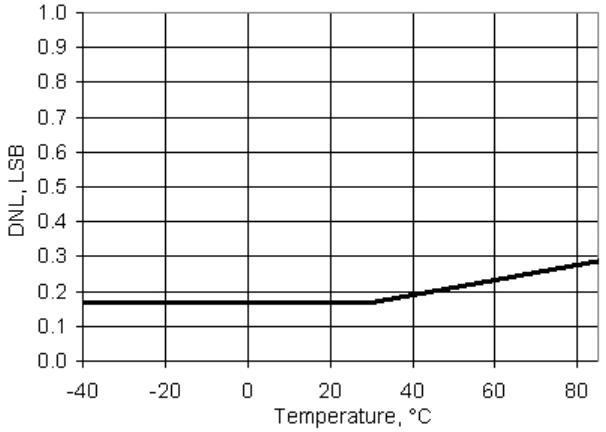


Figure 11-54. VDAC Full Scale Error vs Temperature, 1 V Mode

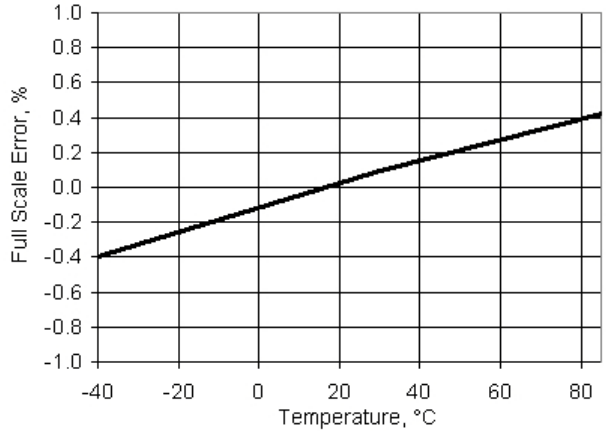


Figure 11-55. VDAC Full Scale Error vs Temperature, 4 V Mode

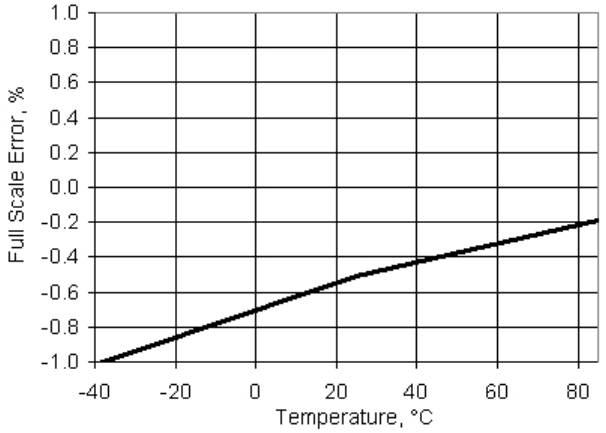


Figure 11-56. VDAC Operating Current vs Temperature, 1V Mode, Low speed mode

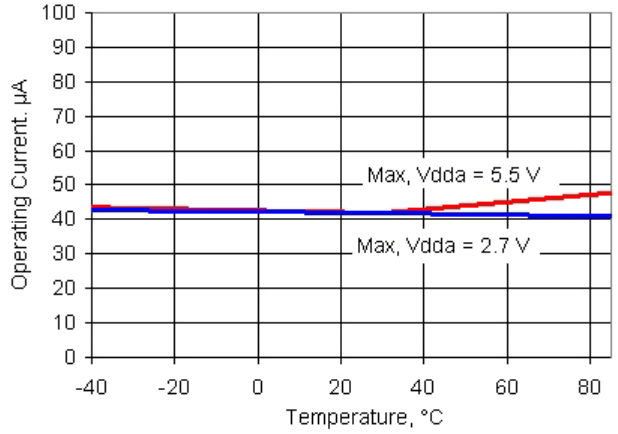
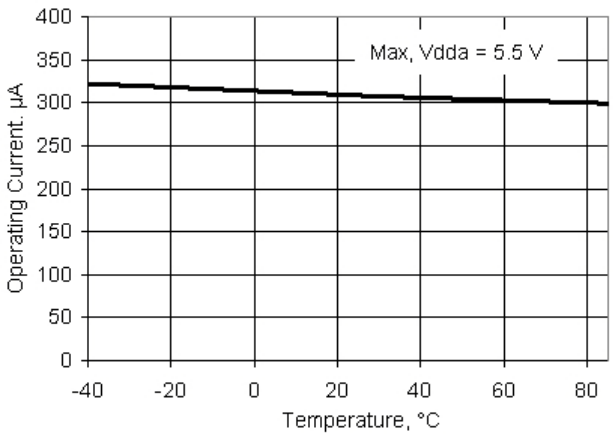


Figure 11-57. VDAC Operating Current vs Temperature, 1 V Mode, High speed mode



11.8.5 SWD Interface

Figure 11-69. SWD Interface Timing

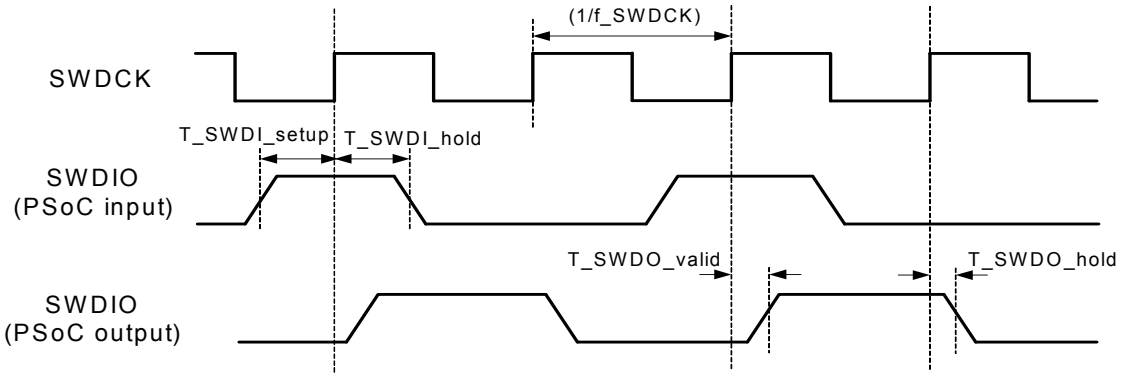


Table 11-71. SWD Interface AC Specifications[77]

Parameter	Description	Conditions	Min	Typ	Max	Units
f_SWDCK	SWDCLK frequency	3.3 V ≤ V_{DDD} ≤ 5 V	–	–	14[78]	MHz
		1.71 V ≤ V_{DDD} < 3.3 V	–	–	7[78]	MHz
		1.71 V ≤ V_{DDD} < 3.3 V, SWD over USBIO pins	–	–	5.5[78]	MHz
T_SWDI_setup	SWDIO input setup before SWDCK high	T = 1/f_SWDCK max	T/4	–	–	–
T_SWDI_hold	SWDIO input hold after SWDCK high	T = 1/f_SWDCK max	T/4	–	–	–
T_SWDO_valid	SWDCK high to SWDIO output	T = 1/f_SWDCK max	–	–	2T/5	–

11.8.6 SWV Interface

Table 11-72. SWV Interface AC Specifications[77]

Parameter	Description	Conditions	Min	Typ	Max	Units
	SWV mode SWV bit rate		–	–	33	Mbit

Notes
77. Based on device characterization (Not production tested).
78. f_SWDCK must also be no more than 1/3 CPU clock frequency.

11.9 Clocking

Specifications are valid for –40 °C ≤ T_A ≤ 85 °C and T_J ≤ 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

11.9.1 Internal Main Oscillator

Table 11-73. IMO DC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
	Supply current					
	62.6 MHz		–	–	600	µA
	48 MHz		–	–	500	µA
	24 MHz – USB mode	With oscillator locking to USB bus	–	–	500	µA
	24 MHz – non USB mode		–	–	300	µA
	12 MHz		–	–	200	µA
	6 MHz		–	–	180	µA
	3 MHz		–	–	150	µA

Figure 11-70. IMO Current vs. Frequency

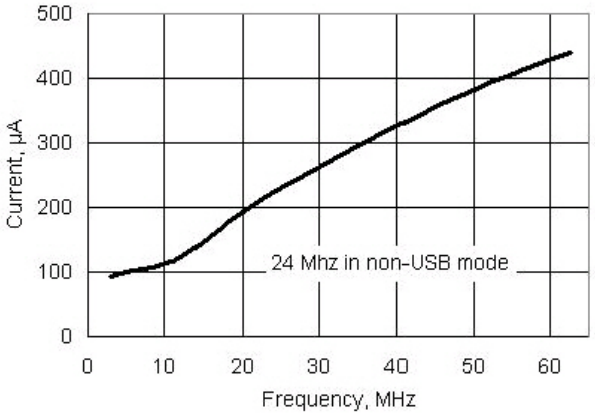


Table 11-74. IMO AC Specifications

Parameter	Description	Conditions	Min	Typ	Max	Units
F_{IMO}[79]	IMO frequency stability (with factory trim)					
	62.6 MHz		–7	–	7	%
	48 MHz		–5	–	5	%
	24 MHz – Non USB mode		–4	–	4	%
	24 MHz – USB mode	With oscillator locking to USB bus	–0.25	–	0.25	%
	12 MHz		–3	–	3	%
	6 MHz		–2	–	2	%
	3 MHz	0 °C to 70 °C	–1	–	1	%
		–40 °C to 85 °C	–1.5	–	1.5	%
	3 MHz frequency stability after typical PCB assembly post-reflow.	Typical (non-optimized) board layout and 250 °C solder reflow. Device may be calibrated after assembly to improve performance.	–	±2	–	%
	Startup time[80]	From enable (during normal system operation)	–	–	13	µs

Notes
79. F_{IMO} is measured after packaging, and thus accounts for substrate and die attach stresses.
80. Based on device characterization (Not production tested).

12. Ordering Information

In addition to the features listed in Table 12-1, every CY8C36 device includes: a precision on-chip voltage reference, precision oscillators, flash, ECC, DMA, a fixed function I²C, 4 KB trace RAM, JTAG/SWD programming and debug, external memory interface, and more. In addition to these features, the flexible UDBs and analog subsection support a wide range of peripherals. To assist you in selecting the ideal part, PSoC Creator makes a part recommendation after you choose the components required by your application. All CY8C36 derivatives incorporate device and flash security in user-selectable security levels; see the TRM for details.

Table 12-1. CY8C36 Family with Single Cycle 8051

Part Number	MCU Core				Analog								Digital				I/O[88]				Package	JTAG ID[89]
	CPU Speed (MHz)	Flash (KB)	SRAM (KB)	EEPROM (KB)	LCD Segment Drive	ADC	DAC	Comparator	SC/CT Analog Blocks[86]	Opamps	DFB	CapSense	UDBs[87]	16-bit Timer/PWM	FS USB	CAN 2.0b	Total I/O	GPIO	SIO	USBIO		
32 KB Flash																						
CY8C3665PVI-008	67	32	4	1	✔	12-bit Del-Sig	4	4	4	2	✔	✔	20	4	–	–	29	25	4	0	48-pin SSOP	0×1E008069
CY8C3665AXI-198	67	32	8	1	✔	12-bit Del-Sig	2	0	0	0	–	✔	16	0	–	–	70	62	8	0	100-pin TQFP	0x1E0C6069
CY8C3665LTI-044	67	32	4	1	✔	12-bit Del-Sig	4	4	4	0	✔	✔	20	4	✔	–	48	38	8	2	68-pin QFN	0x1E02C069
CY8C3665LTI-199	67	32	8	1	✔	12-bit Del-Sig	2	0	0	0	–	✔	16	0	–	–	46	38	8	0	68-pin QFN	0x1E0C7069
CY8C3665FNI-211	67	32	4	1	✔	12-bit Del-Sig	4	4	4	4	✔	✔	20	4	✔	–	48	38	8	2	72 WLCSP	0x1E0D3069
64 KB Flash																						
CY8C3666AXI-052	67	64	8	2	✔	12-bit Del-Sig	4	4	4	4	✔	✔	24	4	–	–	70	62	8	0	100-pin TQFP	0×1E034069
CY8C3666AXI-036	67	64	8	2	✔	12-bit Del-Sig	4	4	4	4	✔	✔	24	4	✔	–	72	62	8	2	100-pin TQFP	0×1E024069
CY8C3666LTI-027	67	64	8	2	✔	12-bit Del-Sig	4	4	4	4	✔	✔	24	4	✔	–	48	38	8	2	68-pin QFN	0×1E01B069
CY8C3666LTI-050	67	64	8	2	✔	12-bit Del-Sig	4	4	4	2	✔	✔	24	4	✔	–	31	25	4	2	48-pin QFN	0×1E032069
CY8C3666AXI-037	67	64	8	2	✔	12-bit Del-Sig	4	4	4	4	✔	✔	24	4	–	✔	70	62	8	0	100-pin TQFP	0×1E025069
CY8C3666AXI-200	67	64	8	2	✔	12-bit Del-Sig	2	2	0	2	–	✔	20	2	–	–	70	62	8	0	100-pin TQFP	0x1E0C8069
CY8C3666LTI-201	67	64	8	2	✔	12-bit Del-Sig	2	2	0	2	–	✔	20	2	–	–	46	38	8	0	68-pin QFN	0x1E0C9069
CY8C3666AXI-202	67	64	8	2	✔	12-bit Del-Sig	4	2	2	2	–	✔	24	4	–	–	70	62	8	0	100-pin TQFP	0x1E0CA069
CY8C3666LTI-203	67	64	8	2	✔	12-bit Del-Sig	4	2	2	2	–	✔	24	4	–	–	46	38	8	0	68-pin QFN	0x1E0CB069

Notes

86. Analog blocks support a wide variety of functionality including TIA, PGA, and mixers. See the Example Peripherals on page 44 for more information on how analog blocks can be used.
87. UDBs support a wide variety of functionality including SPI, LIN, UART, timer, counter, PWM, PRS, and others. Individual functions may use a fraction of a UDB or multiple UDBs. Multiple functions can share a single UDB. See the Example Peripherals on page 44 for more information on how UDBs can be used.
88. The I/O Count includes all types of digital I/O: GPIO, SIO, and the two USB I/O. See the I/O System and Routing on page 37 for details on the functionality of each of these types of I/O.
89. The JTAG ID has three major fields. The most significant nibble (left digit) is the version, followed by a 2 byte part number and a 3 nibble manufacturer ID.

14. Acronyms

Table 14-1. Acronyms Used in this Document

Acronym	Description
abus	analog local bus
ADC	analog-to-digital converter
AG	analog global
AHB	AMBA (advanced microcontroller bus architecture) high-performance bus, an ARM data transfer bus
ALU	arithmetic logic unit
AMUXBUS	analog multiplexer bus
API	application programming interface
APSR	application program status register
ARM®	advanced RISC machine, a CPU architecture
ATM	automatic thump mode
BW	bandwidth
CAN	Controller Area Network, a communications protocol
CMRR	common-mode rejection ratio
CPU	central processing unit
CRC	cyclic redundancy check, an error-checking protocol
DAC	digital-to-analog converter, see also IDAC, VDAC
DFB	digital filter block
DIO	digital input/output, GPIO with only digital capabilities, no analog. See GPIO.
DMA	direct memory access, see also TD
DNL	differential nonlinearity, see also INL
DNU	do not use
DR	port write data registers
DSI	digital system interconnect
DWT	data watchpoint and trace
ECC	error correcting code
ECO	external crystal oscillator
EEPROM	electrically erasable programmable read-only memory
EMI	electromagnetic interference
EMIF	external memory interface
EOC	end of conversion
EOF	end of frame
EPSR	execution program status register
ESD	electrostatic discharge
ETM	embedded trace macrocell

Table 14-1. Acronyms Used in this Document *(continued)*

Acronym	Description
FIR	finite impulse response, see also IIR
FPB	flash patch and breakpoint
FS	full-speed
GPIO	general-purpose input/output, applies to a PSoC pin
HVI	high-voltage interrupt, see also LVI, LVD
IC	integrated circuit
IDAC	current DAC, see also DAC, VDAC
IDE	integrated development environment
I^2C, or IIC	Inter-Integrated Circuit, a communications protocol
IIR	infinite impulse response, see also FIR
ILO	internal low-speed oscillator, see also IMO
IMO	internal main oscillator, see also ILO
INL	integral nonlinearity, see also DNL
I/O	input/output, see also GPIO, DIO, SIO, USBIO
IPOR	initial power-on reset
IPSR	interrupt program status register
IRQ	interrupt request
ITM	instrumentation trace macrocell
LCD	liquid crystal display
LIN	Local Interconnect Network, a communications protocol.
LR	link register
LUT	lookup table
LVD	low-voltage detect, see also LVI
LVI	low-voltage interrupt, see also HVI
LVTTL	low-voltage transistor-transistor logic
MAC	multiply-accumulate
MCU	microcontroller unit
MISO	master-in slave-out
NC	no connect
NMI	nonmaskable interrupt
NRZ	non-return-to-zero
NVIC	nested vectored interrupt controller
NVL	nonvolatile latch, see also WOL
opamp	operational amplifier
PAL	programmable array logic, see also PLD
PC	program counter
PCB	printed circuit board
PGA	programmable gain amplifier

Description Title: PSoC® 3: CY8C36 Family Datasheet Programmable System-on-Chip (PSoC®) *(continued)* Document Number: 001-53413				
Revision	**ECN**	**Submission Date**	**Orig. of Change**	**Description of Change**
*T	4188568	11/14/2013	MKEA	Added SIO Comparator Specifications. Corrected typo in the V_{REF} parameter in the Voltage Reference Specifications. Added CSP information in Packaging and Ordering Information sections. Updated delta-sigma V_{OS} spec conditions.
*U	4385782	05/21/2014	MKEA	Updated General Description and Features. Added More Information and PSoC Creator sections. Updated 100-pin TQFP package diagram.
*V	4708125	03/31/2015	MKEA	Added INL4 and DNL4 specs in VDAC DC Specifications. Updated Figure 6-11. Added second note after Figure 6-4. Added a reference to Fig 6-1 in *Section 6.1.1* and *Section 6.1.2*. Updated *Section 6.2.2*. Added *Section 7.8.1*. Updated Boost specifications.
*W	4807497	06/23/2015	MKEA	Added reference to code examples in More Information. Updated typ value of TWRITE from 2 to 10 in EEPROM AC specs table. Changed “Device supply for USB operation" to "Device supply (VDDD) for USB operation" in USB DC Specifications. Clarified power supply sequencing and margin for VDDA and VDDD. Updated Serial Wire Debug Interface with limitations of debugging on Port 15. Updated Section 11.7.5. Updated Delta-sigma ADC DC Specifications
*X	4932879	09/24/2015	MKEA	Changed the Regulator Output Capacitor min and max from "-" to 0.9 and 1.1, respectively. Added reference to AN54439 in Section 11.9.3. Added MHz ECO DC specs table. Removed references to IPOR rearm issues in Section 6.3.1.1. Table 6-1: Changed DSI Fmax to 33 MHz. Figure 6-1: Changed External I/O or DSI to 0-33 MHz. Table 11-10: Changed Fgpioin Max to 33 MHz. Table 11-12: Changed Fsioin Max to 33 MHz.
*Y	5322536	06/27/2016	MKEA	Updated More Information. Corrected typos in External Electrical Connections. Added links to CAD Libraries in Section 2.